

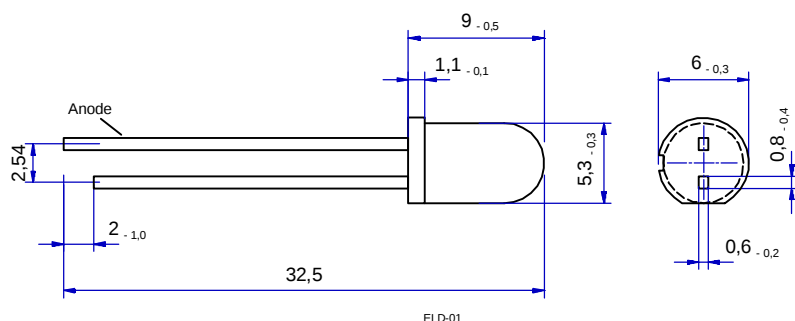
Radiation	Type	Technology	Case
Infrared	ELD-870f-515-2	AlGaAs/AlGaAs	5 mm plastic lens

Description

High-power, high-speed, double heterostructure with removed substrate, chip with frame contact, housing without standoff leads

Applications

Optical communications, safety equipment



Note: Special packages with standoff available on request

$T_{amb} = 25^{\circ}\text{C}$, unless otherwise specified

Parameter	Test conditions	Symbol	Value	Unit
Forward current (DC)		I_F	100	mA
Peak forward current	$(t_P \leq 50 \mu\text{s}, t_P / T = 1/2)$	I_{FM}	200	mA
Surge forward current	$(t_P \leq 10 \mu\text{s})$	I_{FSM}	2000	mA
Reverse voltage	$I_R = 100 \mu\text{A}$	V_R	5	V
Operating temperature range		T_{amb}	-20 to +100	$^{\circ}\text{C}$
Storage temperature range		T_{stg}	-55 to +100	$^{\circ}\text{C}$
Mass		m	0.33	g

Optical and Electrical Characteristics

$T_{amb} = 25^{\circ}\text{C}$, unless otherwise specified

Parameter	Test conditions	Symbol	Min	Typ	Max	Unit
Forward voltage	$I_F = 100 \text{ mA}$	V_F		1.45	2.1	V
Radiant power	$I_F = 100 \text{ mA}$	Φ_e		16		mW
Radiant intensity	$I_F = 100 \text{ mA}$	I_e		75		mW/sr
Peak wavelength	$I_F = 100 \text{ mA}$	λ_p		870		nm
Spectral bandwidth at 50%	$I_F = 100 \text{ mA}$	$\Delta\lambda_{0.5}$		70		nm
Viewing angle		ϕ		8		deg.
Switching time	$I_F = 100 \text{ mA}$	t_r, t_f		5	10	ns